

1. (Cancelled)
2. (Cancelled)
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6. (Cancelled)
7. (Cancelled)
8. (Cancelled)
9. (Cancelled)
10. (Cancelled)

11. (Previously Presented) An alcohol sensor utilizing a work function measurement principle comprising at least one gas-sensitive field-effect transistor which comprises at least one substrate having source and drain areas and at least one gate electrode located at a distance from a gate region between the source and drain areas, said gate electrode being associated with a gas-sensitive layer comprising a polymer or an inorganic metal oxide and wherein the layer is applied separately to the substrate such that it is substantially opposite a gate region of the field-effect transistor thereby forming a gap there between, wherein the gas-sensitive layer comprises a polymer and is selected from the group consisting of polysiloxane or a polysilsesquioxane derivative, wherein the polysilsesquioxane derivative is polycyclopentylsilsesquioxane.

12. (Previously Presented) An alcohol sensor utilizing a work function measurement principle comprising:

at least one gas-sensitive field-effect transistor which comprises at least one substrate having source and drain areas, at least one gate electrode located at a distance from the source and drain areas,

and a gas-sensitive layer, wherein the gas-sensitive layer comprises polycyclopentylsilsesquioxane.

13. (Cancelled)

14. (Previously Presented) The alcohol sensor of claim 12, where the gas-sensitive layer is adjacent to the gate electrode.

15. (Previously Presented) The alcohol sensor of claim 12, where the gas-sensitive layer is adjacent to the source and drain areas.